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(54) Title: A NANOGAP ELECTRODE DEVICE, A METHOD OF MAKING A NANOGAP ELECTRODE DEVICE, AND A SENSOR FOR DETECTING A TARGET ANALYTE

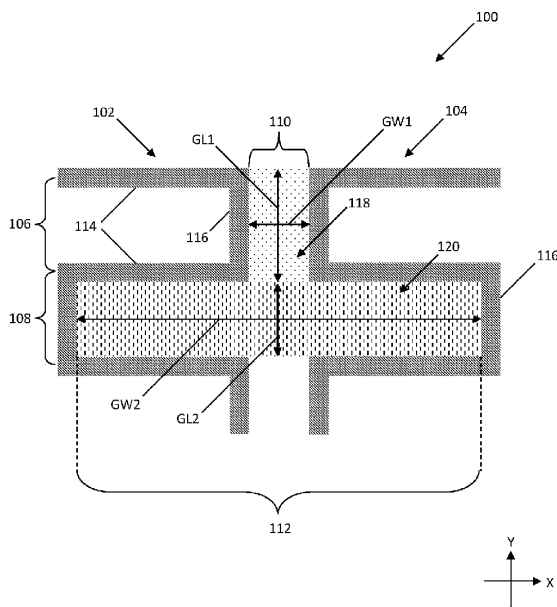


FIG. 1

(57) Abstract: There is provided a nanogap electrode device, a method of making a nanogap electrode device, and a sensor for detecting a target analyte, the nanogap electrode device comprising, a first electrode and a second electrode spaced apart from each other, said first and second electrodes defining a first region and a second region; wherein the first region comprises a first gap between the first electrode and the second electrode, said first gap having a first gap length and a first gap width; wherein the second region comprises a second gap between the first electrode and the second electrode, said second gap having a second gap length and a second gap width; and wherein the second gap length and second gap width are greater than the first gap width.

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